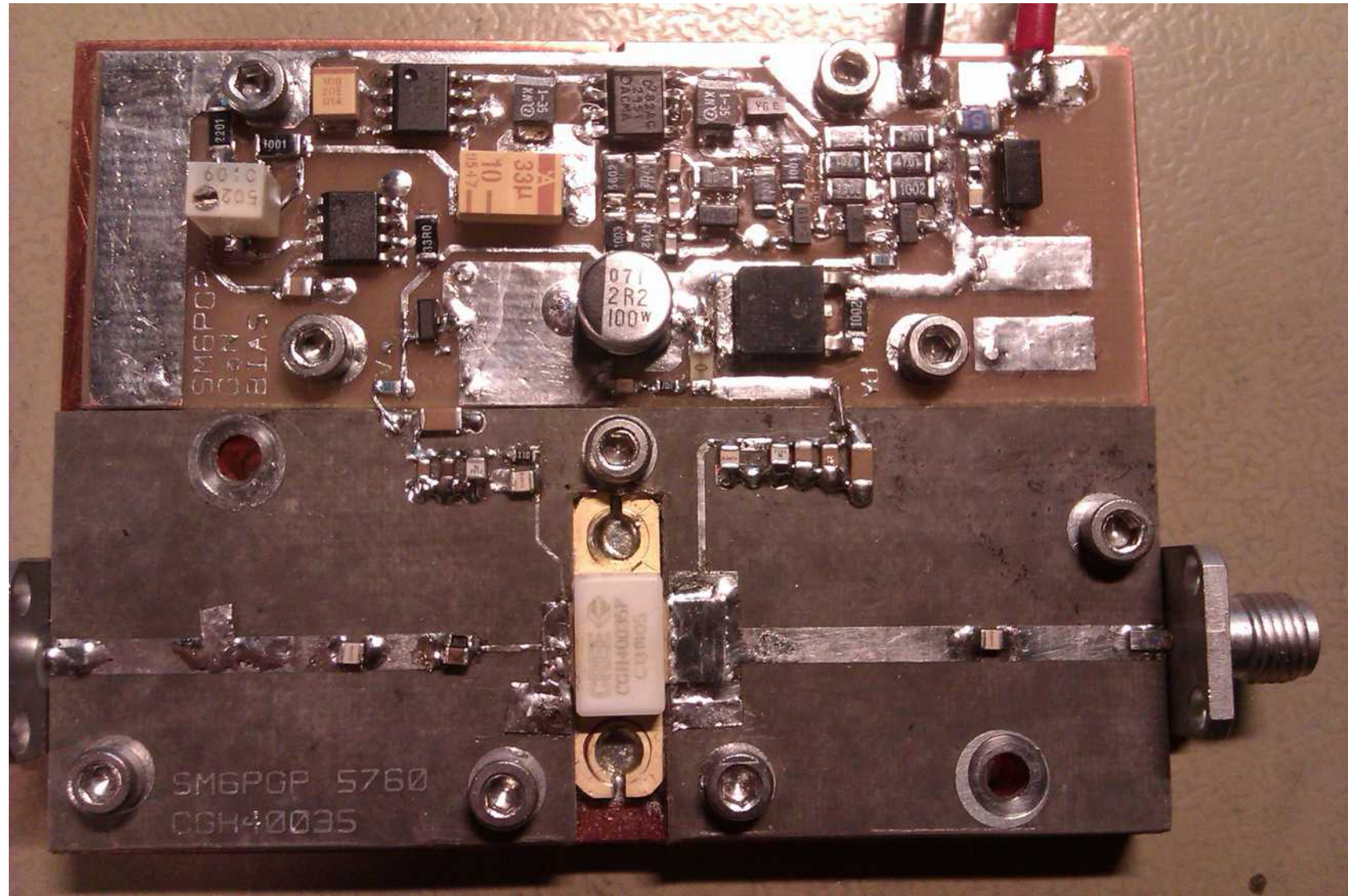
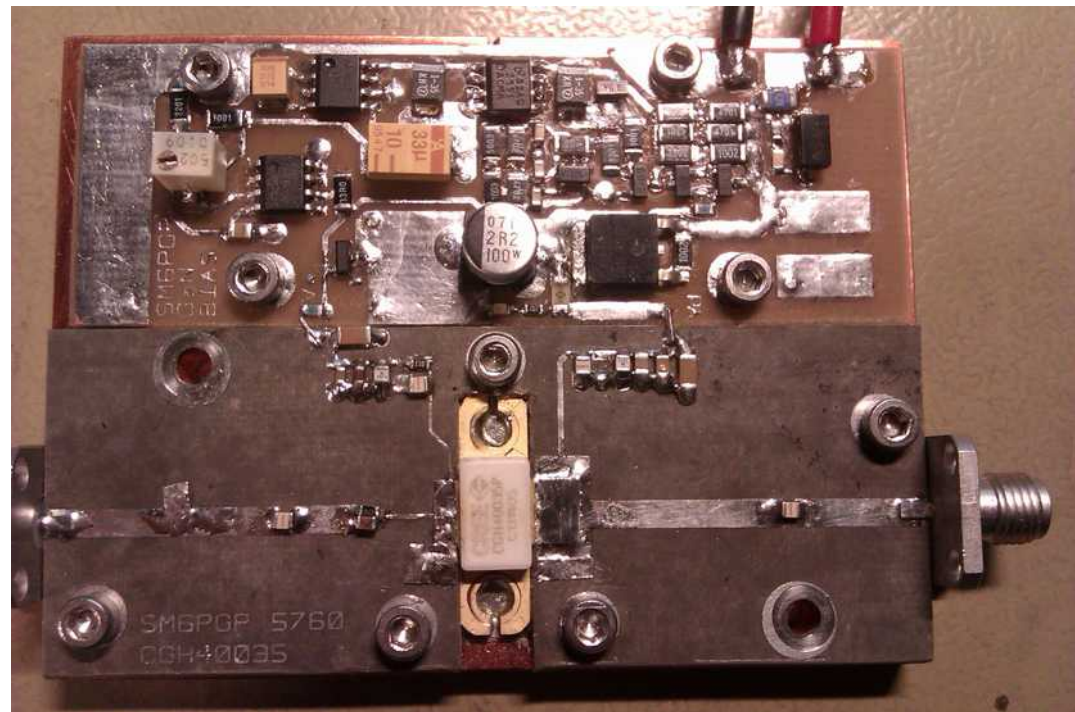


Experiments with GaN devices for 5760 MHz



Experiments with GaN devices for 5760 MHz

- * Devices CREE, 1 st generation devices, general purpose 28V
- * Bias circuit
- * Simulations
- * Measurements
- * 2 devices combined



Experiments with GaN devices for 5760 MHz

- * Devices : CREE, 1 st generation devices, general purpose 28V
- * CGH40006P, 6W, die CGH60008D, approx 75 euro
- * CGH55015, 15W, die CGH60015D, approx 90 euro
- * CGH55030, 30W, die CGH60030D, approx 120 euro
- * CGH40035, 35W, actually 3 x 15W die CGH60015D larger package approx 200 euro
- * CGH40045 tested but no good results, probably a 60 W die ?

Devices available at Digikey.

(2nd gen CGHV1F006 and CGHV1F025 but package is difficult to handle – 3 x 4 mm DFN)
(Should give good performance at 10 GHz, 40 V devices)

Experiments with GaN devices for 5760 MHz

- * Have built several amplifiers
- * single CGH40006 running at 28V – performance OK -
- * single CGH55015 increased voltage to 36V – OK
- * dual stage with 55015 – combined with Anaren 90 deg hybrids 1M803, max 43.7dBm (23W) was used at initial 6 cm tests at SM6FHZ, designed for 28 V but where run at 36 V
- * redesign of the CGH40006 optimized for running at 48V, achieved 12.8 W
- * single CGH55030 – 48 V
- * dual CGH55030 – 48V – 80 W (in use at SM6PGP)
- * single CGH40035 – 48V – 50W (in use at SM6CKU) and one built by Franta OK1CA
- * dual CGH40035 – 48V – 100W (in use at SM6FHZ)

Experiments with GaN devices for 5760 MHz

GaN bias circuit

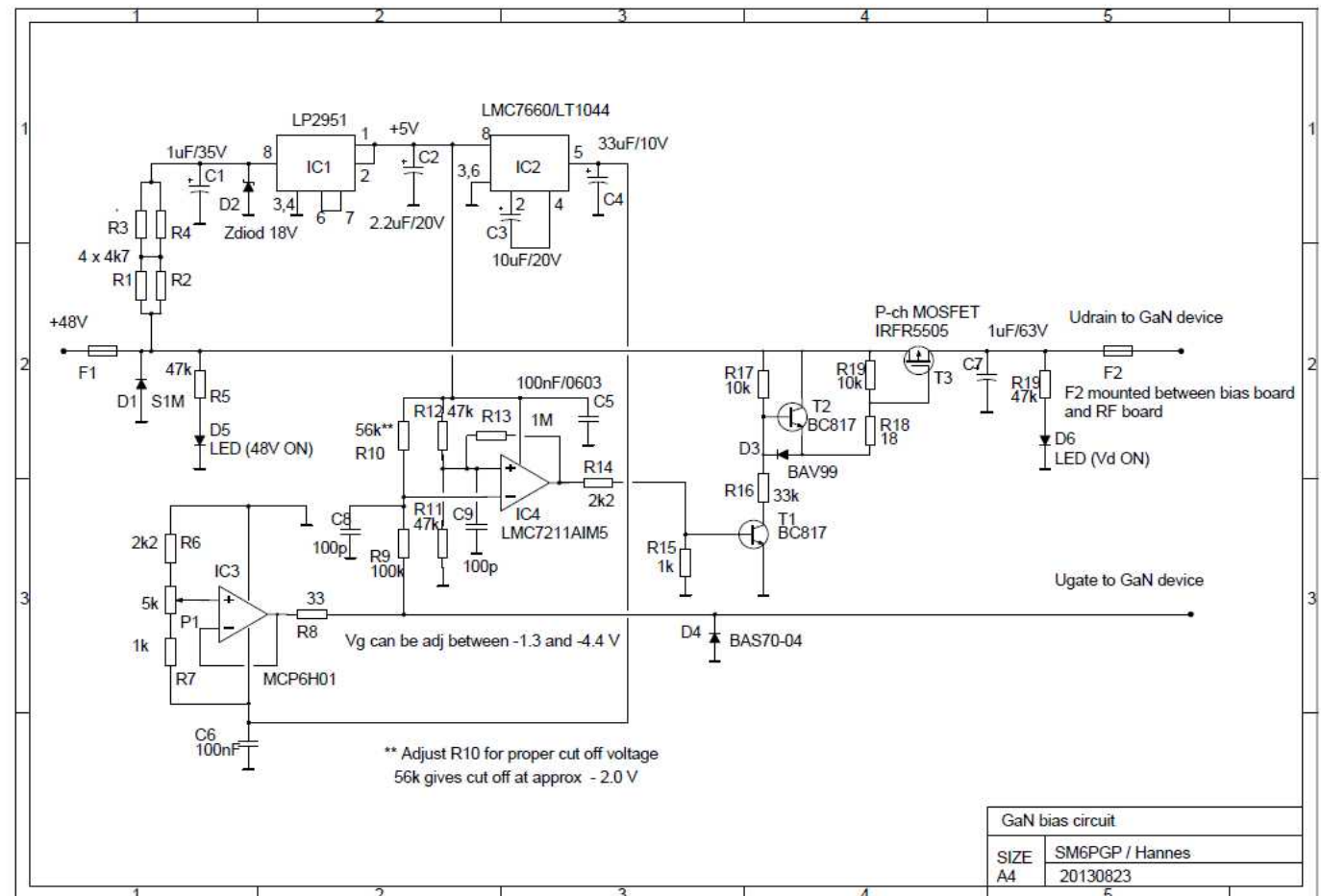
Generates neg voltage

Turn on/off timing

red/black....human error.

Negative voltage failure

Gate voltage constant –
even if device goes into
compression.

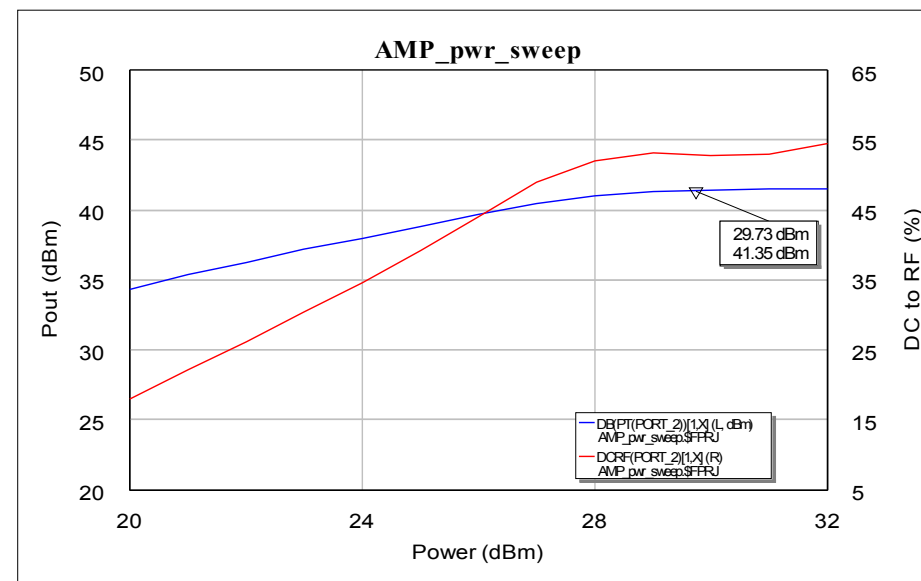
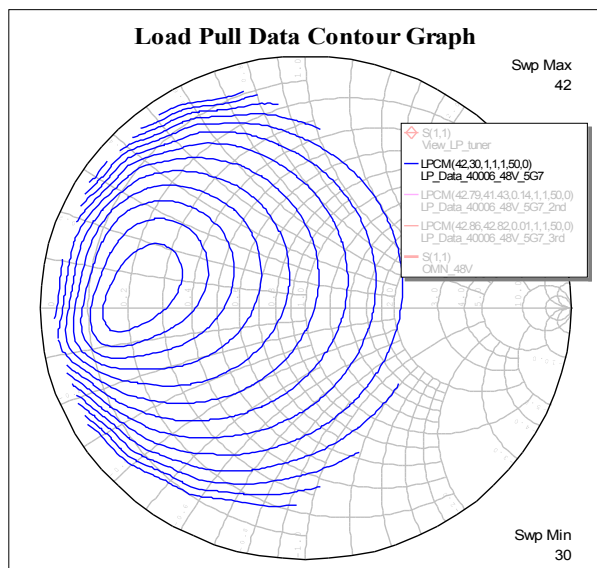
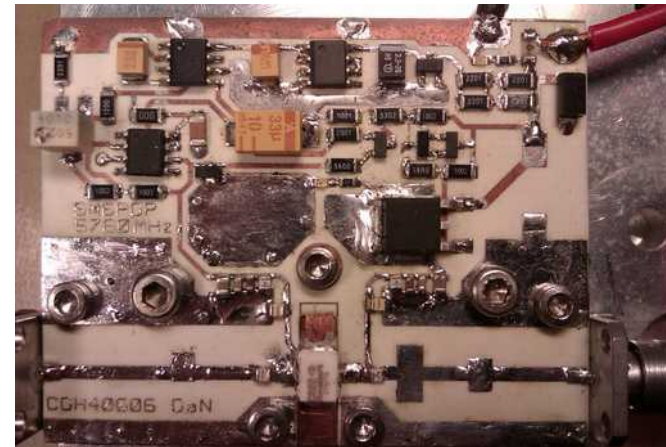


Experiments with GaN devices for 5760 MHz

* simulation of the CGH40006P at 48V – approx 41 dBm should be possible

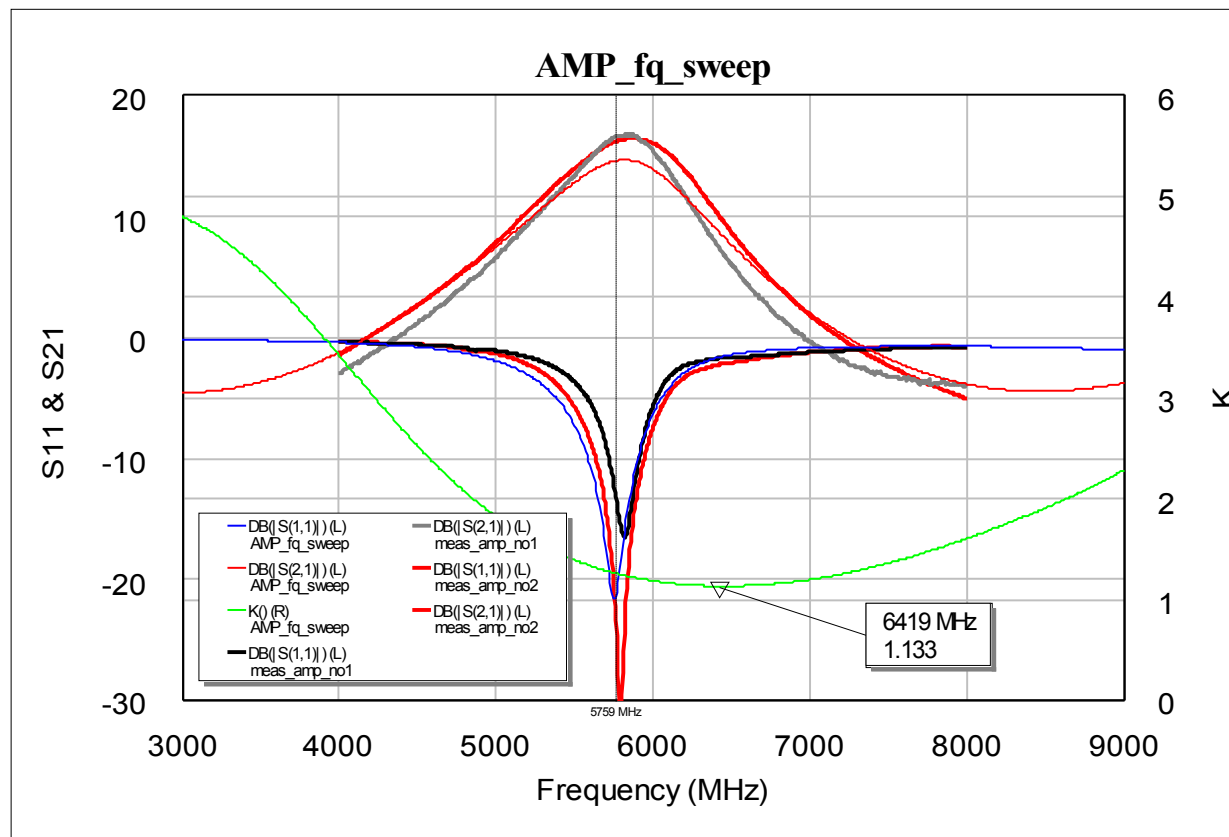
* But running

28V devices at 48V ?



Experiments with GaN devices for 5760 MHz

- * two "drivers" has been built with the CGH40006P at 48V
- * simulations and measurements agree very well



Small signal S11 and S21

Experiments with GaN devices for 5760 MHz

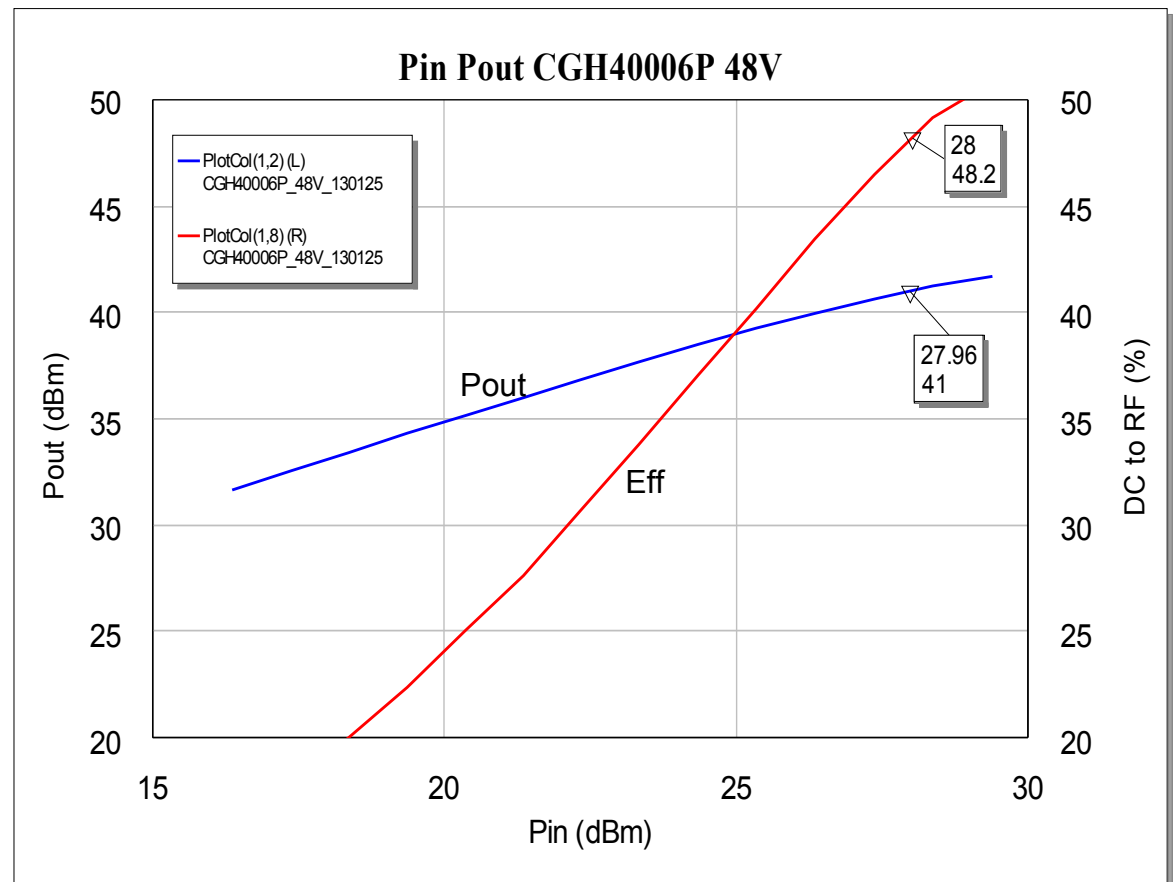
- * measured output power up to 14 W
- * left it running at 12W output , key down for several hours (at 48V)
- * no degradation seen

$V_{br} = 120V$

Violating the junction temp spec. of 225 C.

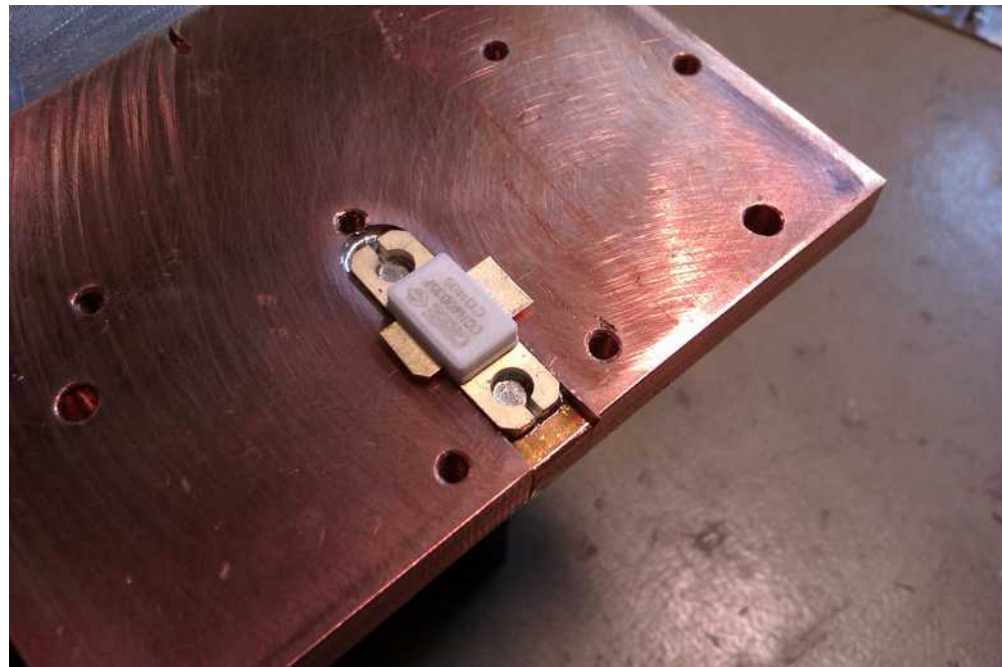
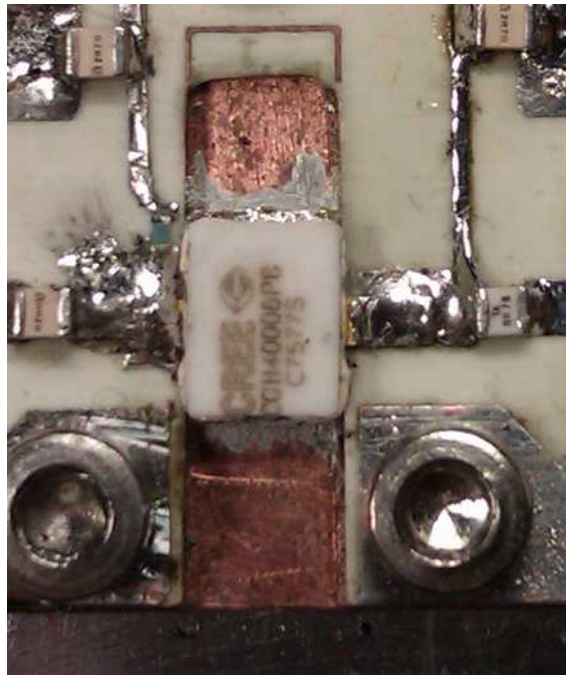
...but we dont need MTTF figures of 10-20 miljon hours

We can let the junction temp reach higher values and still have MTTF figures good enough for HAM operation.



Experiments with GaN devices for 5760 MHz

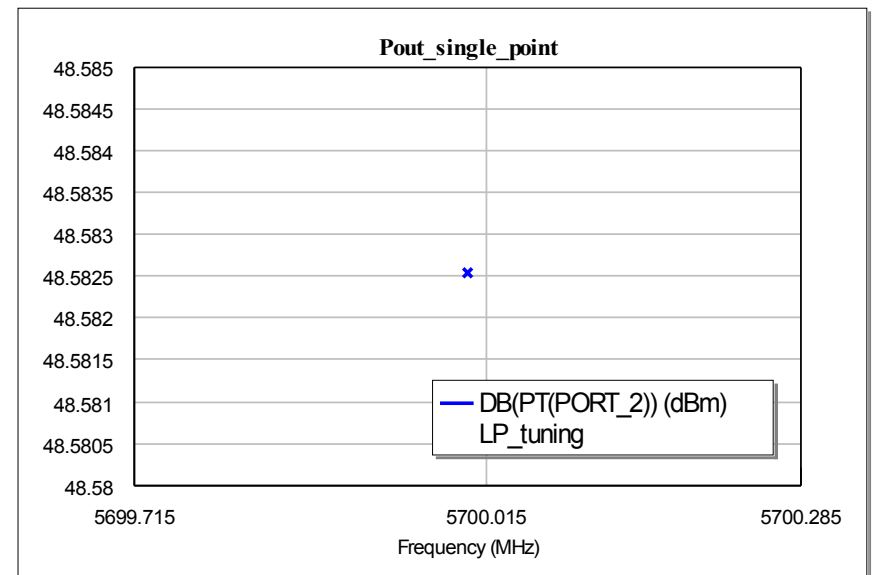
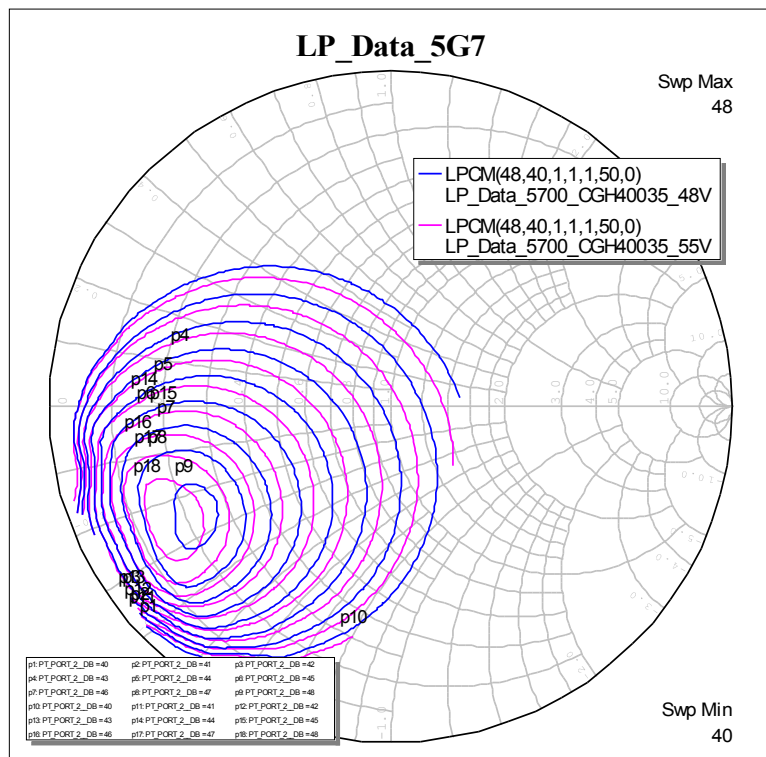
- * keeping junction temperature down
- * soldering devices to copper carrier for best possible heat transfer – and there is no other possibility with a "pill" package
- * pre tin all surfaces to be soldered, use kapton tape and temperature controlled heat bed



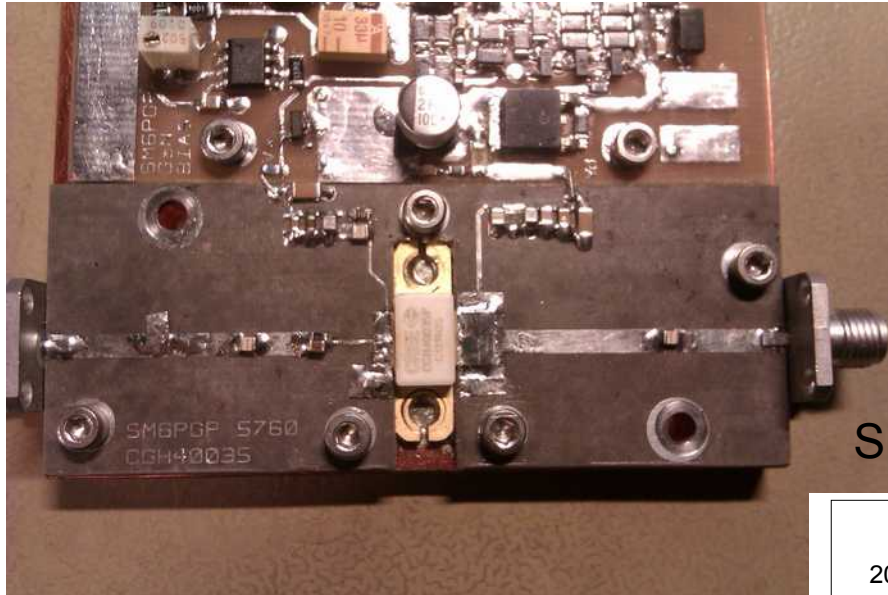
Experiments with GaN devices for 5760 MHz

- * Promising results with the 6 W device – then what about the CGH40035 ?
- * simulations showed promising results – possible with up to 60 W + ?
...but there is no smoke in the simulator !

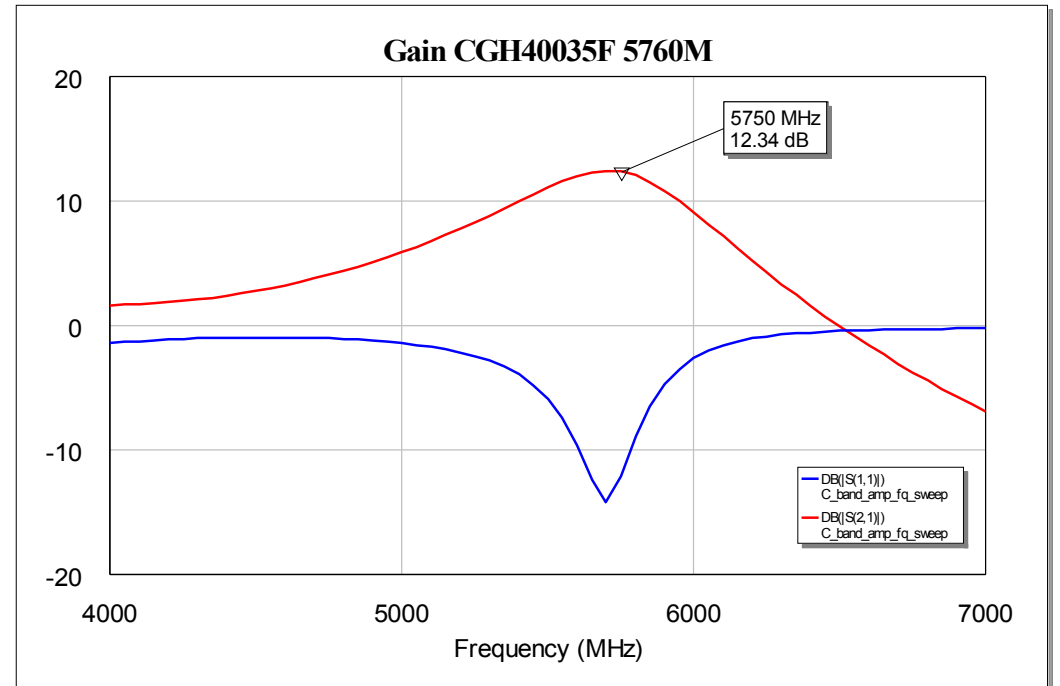
Lets build and find out where is the damage level is !



Experiments with GaN devices for 5760 MHz

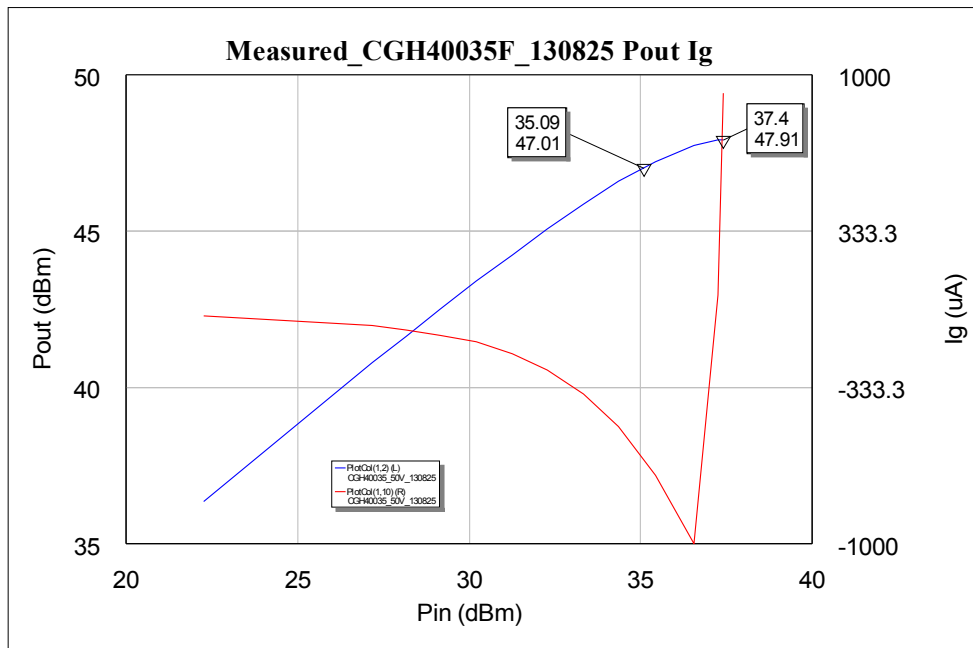
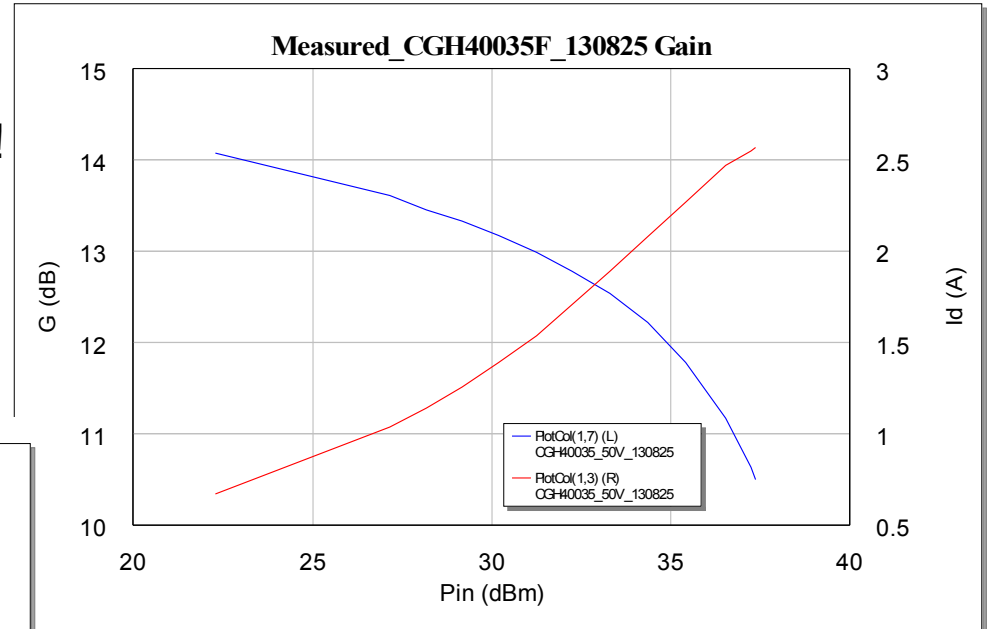


Simulated small signal gain and input matching



Experiments with GaN devices for 5760 MHz

- * Single stage CGH40035F
– real world !
- * at approx 75 W – the smoke gets out !
- * GaN HEMT gate current changes sign when device goes into compression

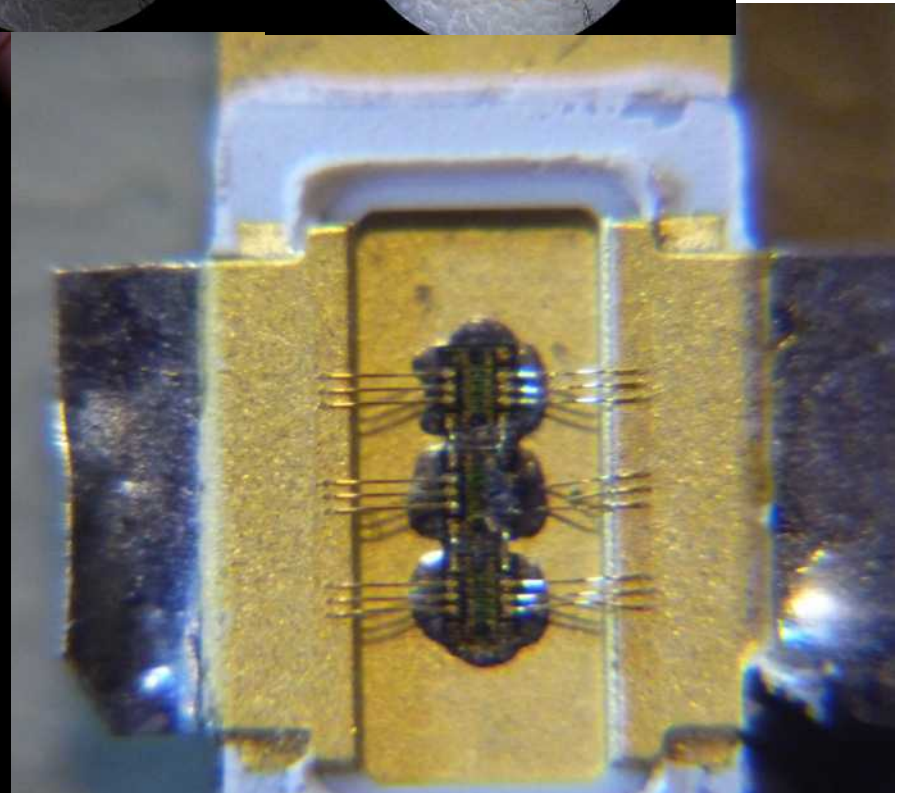
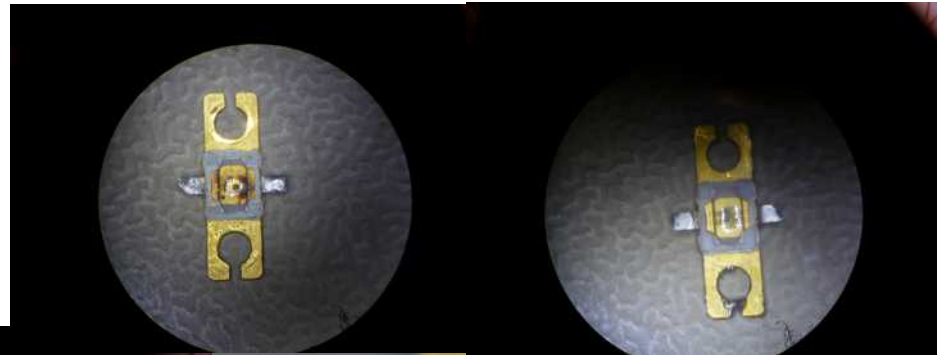


In use at SM6CKU, Ben, so far
no failures !

Experiments with GaN devices for 5760 MHz

* 15 W and 30 W devices – killed of different reasons
Human error, unexpected snow !

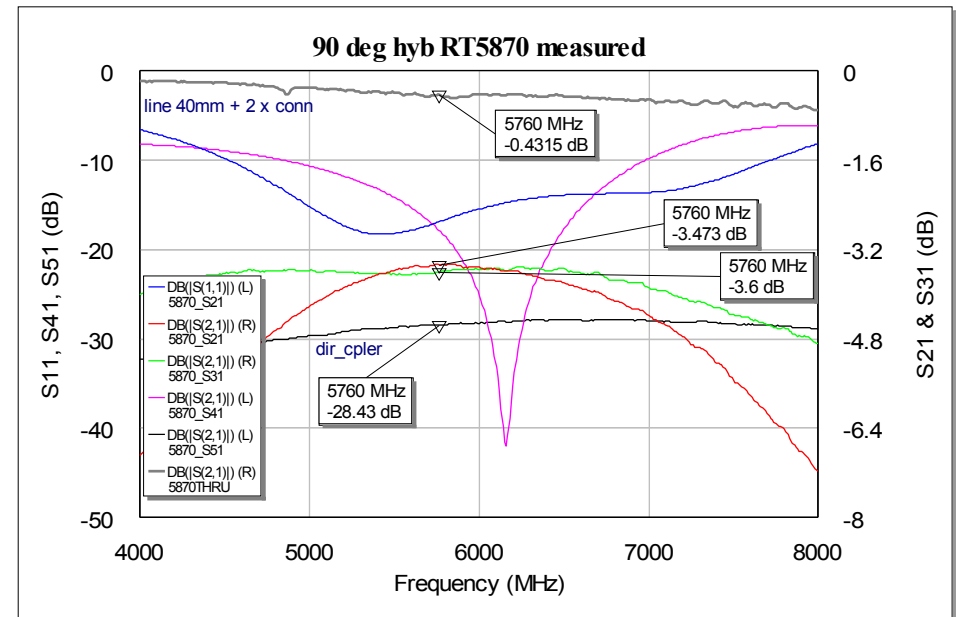
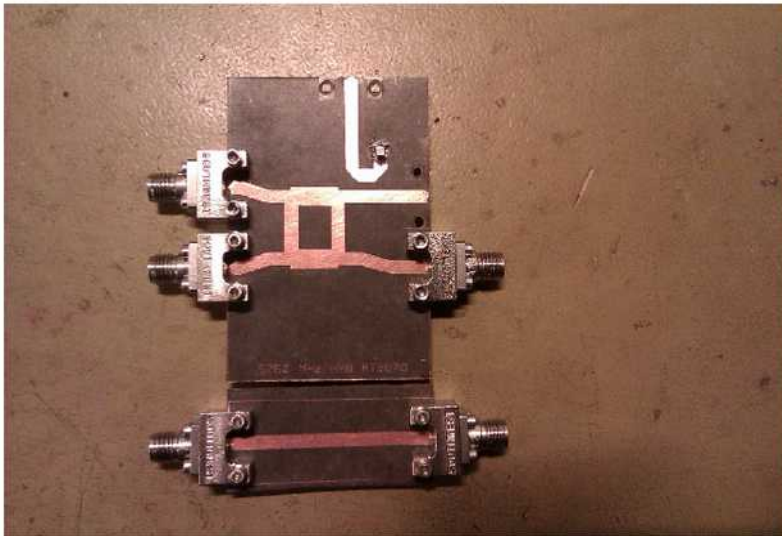
* a dead CGH40035 – killed
– at approx 75 - 80 W out probably
due to excessive heat the die in the
centre gave up !



Experiments with GaN devices for 5760 MHz

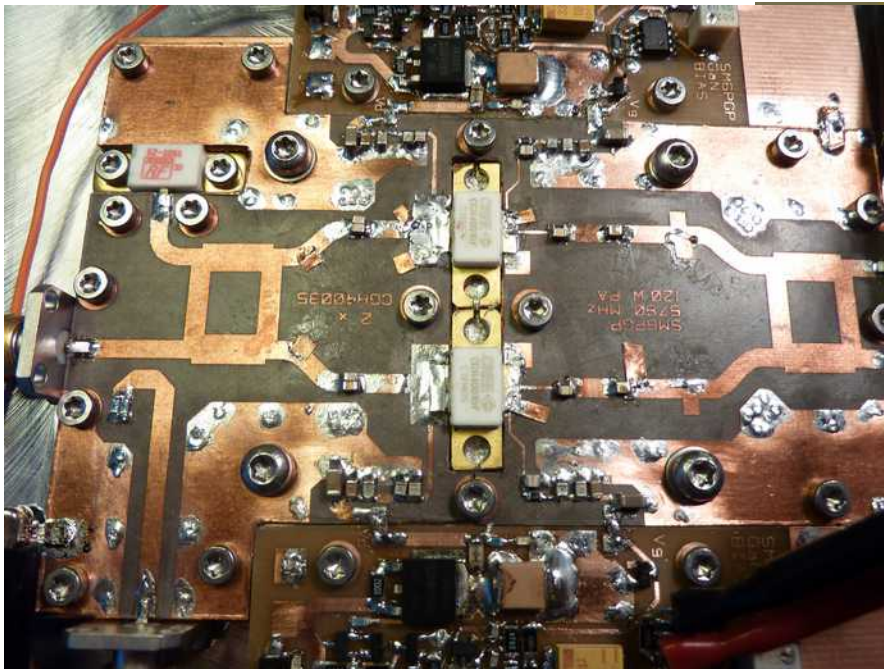
- * Dual stage CGH55030 and CGH40035F
- * Anaren 90 deg hybrids, max 20 W – need something better...
- * design on RT5870 , 31 mil, low loss, IL approx 0.2 dB

90 deg hybrid 5760MHz with 30 dB directional coupler

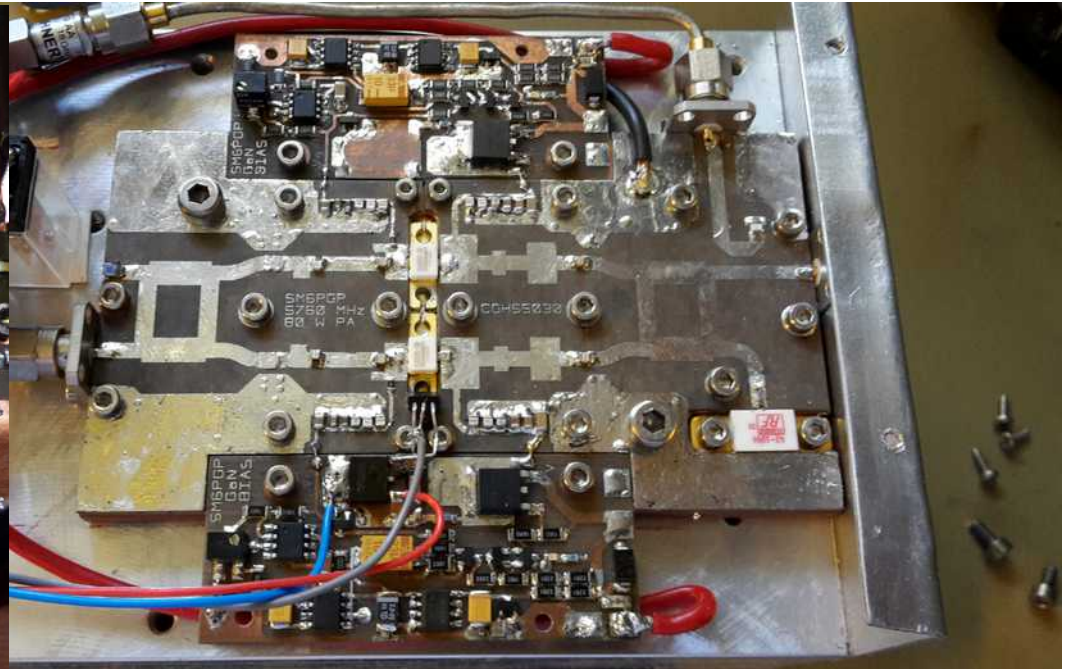


Experiments with GaN devices for 5760 MHz

- * Dual stage CGH55030 and CGH40035F
- * 2 x CGH55030 – built by SM6PGP – 80 W
- * 2 x CGH40035F – built by SM6FHZ – 100 W

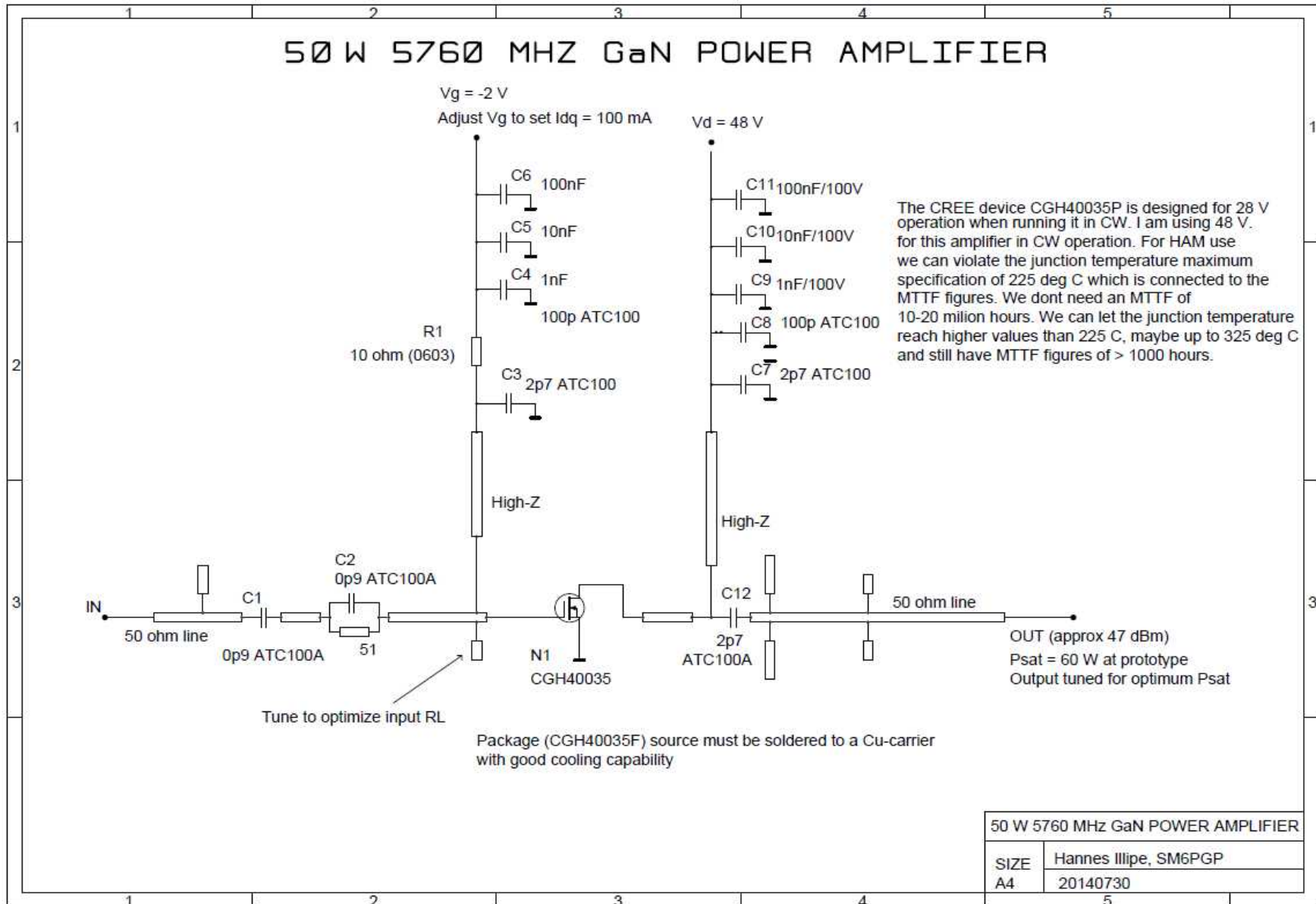


Dual stage CGH40035F, SM6FHZ

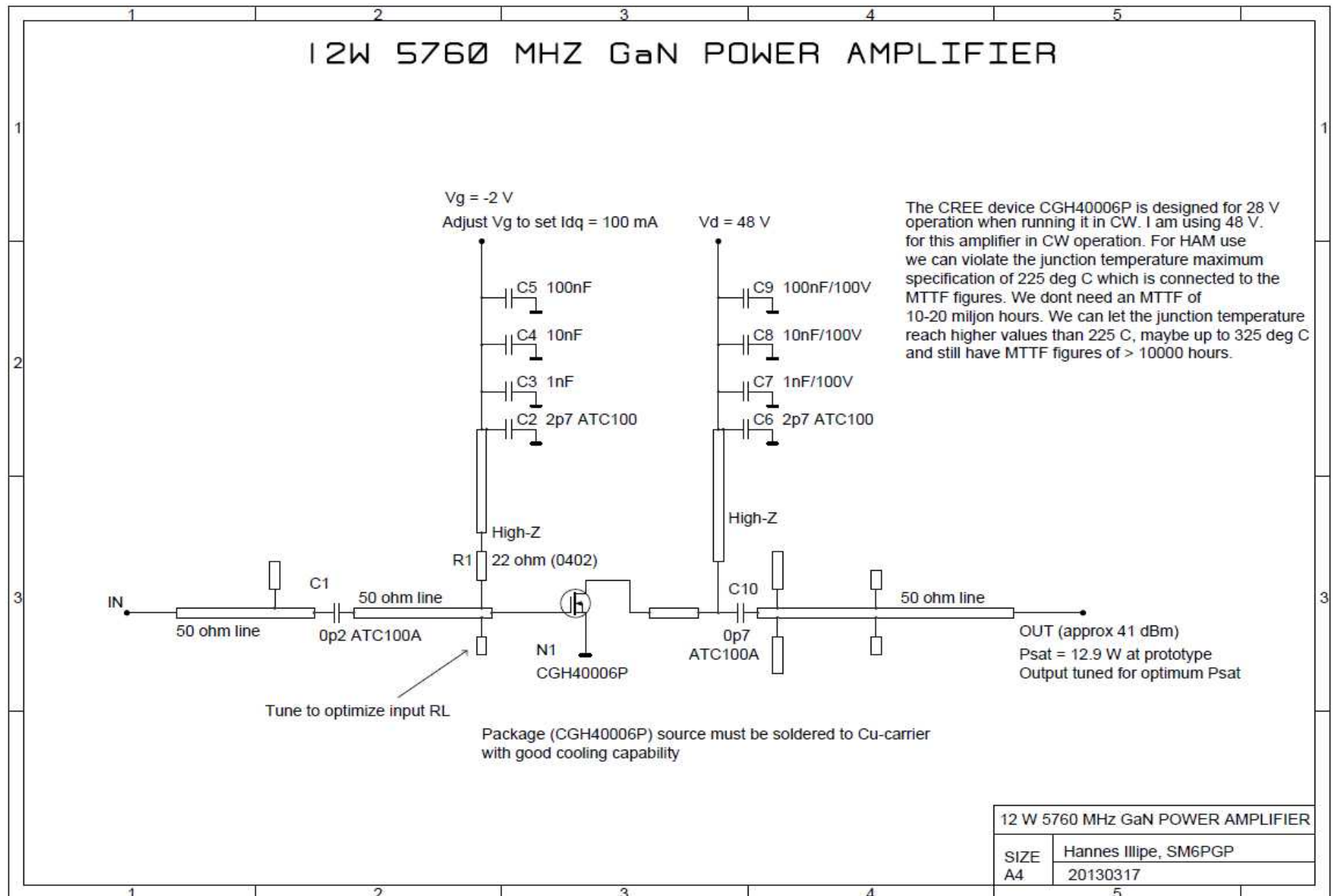


Dual stage CGH55030F, SM6PGP

Experiments with GaN devices for 5760 MHz



Experiments with GaN devices for 5760 MHz



THANK YOU !

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